## MCH6437

# Power MOSFET 20V, $24m\Omega$ , 7A, Single N-Channel



www.onsemi.com

#### **Features**

- Low On-Resistance
- 1.8V Drive
- ESD Diode-Protected Gate
- Pb-Free and RoHS Compliance

VDSS	R <sub>DS</sub> (on) Max	ID Max
	24mΩ@ 4.5V	
20V	35mΩ@ 2.5V	7A
	65mΩ@ 1.8V	

#### **Specifications**

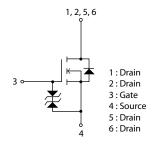
**Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V <sub>DSS</sub>	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ID	7	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I <sub>DP</sub>	28	А
Power Dissipation When mounted on ceramic substrate (1200mm²× 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

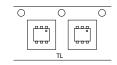
#### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient			
When mounted on ceramic substrate	$R_{\theta JA}$	83.3	°C/W
$(1200 \text{mm}^2 \times 0.8 \text{mm})$			

### Electrical Connection N-Channel



#### Packing Type: TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

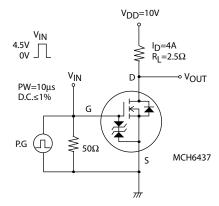
#### MCH6437

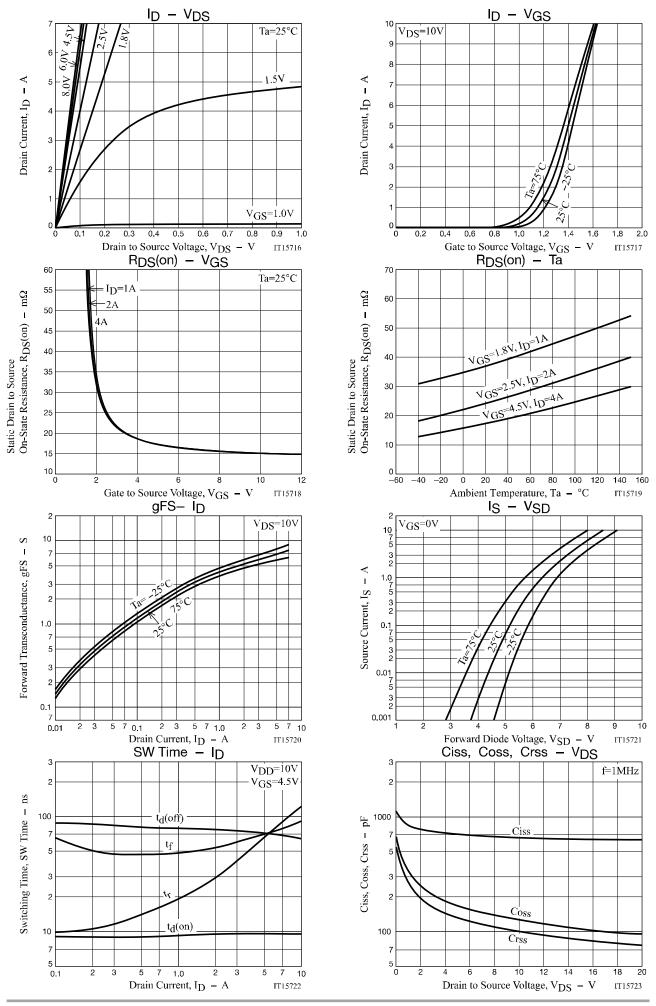
#### **Electrical Characteristics** at Ta = 25°C

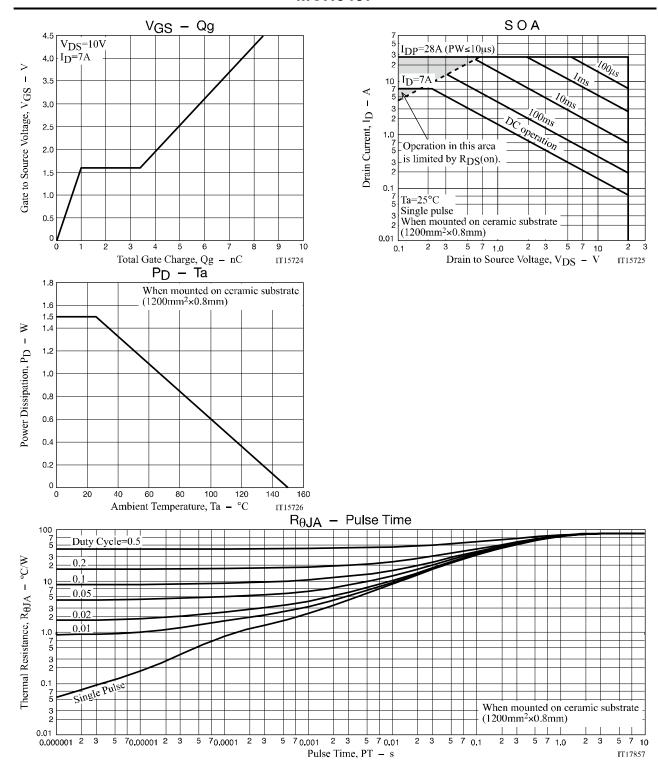
Parameter	Symbol	Conditions	Value			11.2
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =4A		6.2		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =4A, V <sub>GS</sub> =4.5V		18	24	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =2A, V <sub>GS</sub> =2.5V		25	35	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1A, V <sub>GS</sub> =1.8V		38	65	mΩ
Input Capacitance	Ciss			660		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		125		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			9.7		ns
Rise Time	t <sub>r</sub>			53		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		72		ns
Fall Time	tf	1		65		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =7A		8.4		nC
Gate to Source Charge	Qgs			1.0		nC
Gate to Drain "Miller" Charge	Qgd	]		2.4		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =7A, V <sub>GS</sub> =0V		0.81	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **Switching Time Test Circuit**







5 7 0.01

2 3

5 7 0.1

2 3

5 7 1.0

2 3 5 7 10 IT17857

5 70.00001 2 3

5 70.0001 2 3

#### **Package Dimensions**

MCH6437-TL-E / MCH6437-TL-W

#### MCPH6

CASE 419AS ISSUE O

unit: mm

1: Drain

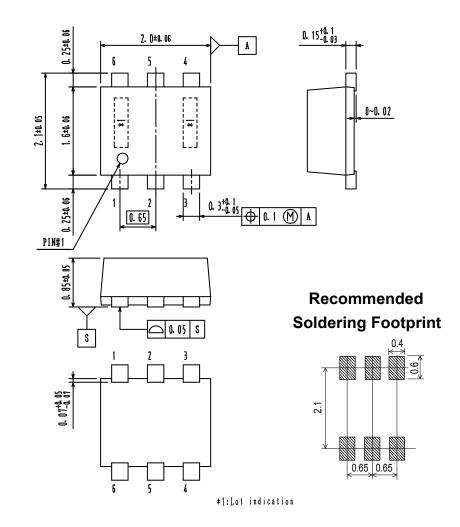
2: Drain

3: Gate

4 : Source

5: Drain

6: Drain



#### ORDERING INFORMATION

Device	Package	Shipping	Note
MCH6437-TL-E	MCPH6	0.000 vvv /Tvvv 0.Dvvl	Pb-Free
MCH6437-TL-W	SC-88FL,SC-70-6,SOT-363	3,000 pcs. / Tape & Reel	Pb-Free and Halogen Free

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6437 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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